

# Kwangeun Kim

## List of Publications by Year in descending order

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25  
papers

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759233

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752698

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27  
docs citations

27  
times ranked

495  
citing authors

#	ARTICLE	IF	CITATIONS
1	226-nm AlGaIn/AlN UV LEDs using p-type Si for hole injection and UV reflection. Applied Physics Letters, 2018, 113, .	3.3	59
2	229-nm UV LEDs on aluminum nitride single crystal substrates using p-type silicon for increased hole injection. Applied Physics Letters, 2018, 112, .	3.3	52
3	Efficiency enhancement of InGaIn/GaN blue light-emitting diodes with top surface deposition of AlN/Al <sub>2</sub> O <sub>3</sub> . Nano Energy, 2018, 43, 259-269.	16.0	31
4	Transferrable single crystalline 4H-SiC nanomembranes. Journal of Materials Chemistry C, 2017, 5, 264-268.	5.5	30
5	Sol-Gel Processed Yttrium-Doped SnO <sub>2</sub> Thin Film Transistors. Electronics (Switzerland), 2020, 9, 254.	3.1	29
6	Band-Bending of Ga-Polar GaN Interfaced with Al <sub>2</sub> O <sub>3</sub> through Ultraviolet/Ozone Treatment. ACS Applied Materials & Interfaces, 2017, 9, 17576-17585.	8.0	25
7	Extremely bias stress stable enhancement mode sol-gel-processed SnO <sub>2</sub> thin-film transistors with Y <sub>2</sub> O <sub>3</sub> passivation layers. Applied Surface Science, 2021, 559, 149971.	6.1	20
8	Effect of Annealing Environment on the Performance of Sol-gel-Processed ZrO <sub>2</sub> RRAM. Electronics (Switzerland), 2019, 8, 947.	3.1	18
9	Reduction of Leakage Current in GaN Schottky Diodes Through Ultraviolet/Ozone Plasma Treatment. IEEE Electron Device Letters, 2019, 40, 1796-1799.	3.9	18
10	Effect of Mg Doping on the Electrical Performance of a Sol-Gel-Processed SnO <sub>2</sub> Thin-Film Transistor. Electronics (Switzerland), 2020, 9, 523.	3.1	16
11	Effect of Annealing Ambient on SnO <sub>2</sub> Thin Film Transistors Fabricated via An Ethanol-based Sol-gel Route. Electronics (Switzerland), 2019, 8, 955.	3.1	15
12	AlGaIn/GaN Schottky-Gate HEMTs With UV/O <sub>3</sub> -Treated Gate Interface. IEEE Electron Device Letters, 2020, 41, 1488-1491.	3.9	13
13	Enhancement Mode Flexible SnO <sub>2</sub> Thin Film Transistors Via a UV/Ozone-Assisted Sol-Gel Approach. IEEE Access, 2020, 8, 123013-123018.	4.2	10
14	Performance Optimization of Nitrogen Dioxide Gas Sensor Based on Pd-AlGaIn/GaN HEMTs by Gate Bias Modulation. Micromachines, 2021, 12, 400.	2.9	9
15	Environmentally and Electrically Stable Sol-gel-Deposited SnO <sub>2</sub> Thin-Film Transistors with Controlled Passivation Layer Diffusion Penetration Depth That Minimizes Mobility Degradation. ACS Applied Materials & Interfaces, 2022, 14, 10558-10565.	8.0	9
16	Photolithography-Based Nanopatterning Using Re-entrant Photoresist Profile. ACS Applied Materials & Interfaces, 2018, 10, 8117-8123.	8.0	8
17	Metal-Al <sub>2</sub> O <sub>3</sub> -GaN capacitors with an ultraviolet/ozone plasma-treated interface. Japanese Journal of Applied Physics, 2020, 59, 030908.	1.5	8
18	Enhanced Switching Reliability of Sol-gel-Processed Y <sub>2</sub> O <sub>3</sub> RRAM Devices Based on Y <sub>2</sub> O <sub>3</sub> Surface Roughness-Induced Local Electric Field. Materials, 2022, 15, 1943.	2.9	8

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19	Flexible Sol-Gel-Processed Y2O3 RRAM Devices Obtained via UV/Ozone-Assisted Photochemical Annealing Process. <i>Materials</i> , 2022, 15, 1899.	2.9	8
20	Analysis on Trap States in p-Metal-Oxide-Semiconductor Capacitors with Ultraviolet/Ozone-Treated GaN Interfaces Through Frequency-Dispersion Capacitance-Voltage Measurements. <i>Electronic Materials Letters</i> , 2020, 16, 140-145.	2.2	4
21	Improving Ni/GaN Schottky diode performance through interfacial passivation layer formed via ultraviolet/ozone treatment. <i>Current Applied Physics</i> , 2020, 20, 293-297.	2.4	4
22	Polarization-Charge Inversion at Al2O3/GaN Interfaces through Post-Deposition Annealing. <i>Electronics (Switzerland)</i> , 2020, 9, 1068.	3.1	4
23	Room-Temperature High-Detectivity Flexible Near-Infrared Photodetectors with Chalcogenide Silver Telluride Nanoparticles. <i>ACS Omega</i> , 2022, 7, 10262-10267.	3.5	4
24	Improved conduction in GaN Schottky junctions with HfO2 passivation layers through post-deposition annealing. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 030902.	1.5	2
25	Investigation in the Ga2O3 passivation layer formed as GaN Schottky barrier through UV/O3 treatment. <i>Results in Physics</i> , 2020, 16, 102964.	4.1	2